

Dual General Purpose Transistors

NPN Duals

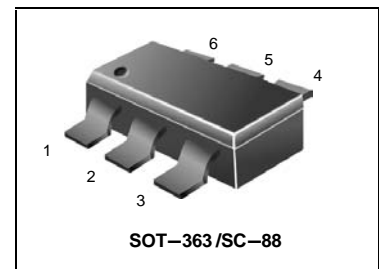
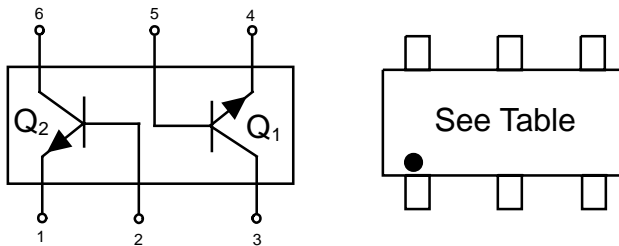
These transistors are designed for general purpose amplifier applications. They are housed in the SOT-363/SC-88 which is designed for low power surface mount applications.

We declare that the material of product compliance with RoHS requirements.

S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

LBC846ADW1T1G
LBC846BDW1T1G
LBC847BDW1T1G
LBC847CDW1T1G
LBC848BDW1T1G
LBC848CDW1T1G

S-LBC846ADW1T1G
S-LBC846BDW1T1G
S-LBC847BDW1T1G
S-LBC847CDW1T1G
S-LBC848BDW1T1G
S-LBC848CDW1T1G



MAXIMUM RATINGS

Rating	Symbol	BC846	BC847	BC848	Unit
Collector-Emitter Voltage	V_{CEO}	65	45	30	V
Collector-Base Voltage	V_{CBO}	80	50	30	V
Emitter-Base Voltage	V_{EBO}	6.0	6.0	5.0	V
Collector Current -Continuous	I_C	100	100	100	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation	P_D	380	mW
Per Device		250	mW
FR-5 Board, (1) $T_A = 25^\circ\text{C}$			
Derate above 25°C		3.0	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	328	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{slg}	-55 to +150	$^\circ\text{C}$

1. FR-5 = 1.0 x 0.75 x 0.062 in.

ORDERING INFORMATION

Device	Marking	Shipping
LBC846ADW1T1G	1A	3000 Units/Reel
LBC846ADW1T3G	1A	10000 Units/Reel
LBC846BDW1T1G	1B	3000 Units/Reel
LBC846BDW1T3G	1B	10000 Units/Reel
LBC847BDW1T1G	1F	3000 Units/Reel
LBC847BDW1T3G	1F	10000 Units/Reel
LBC847CDW1T1G	1G	3000 Units/Reel
LBC847CDW1T3G	1G	10000 Units/Reel
LBC848BDW1T1G	1K	3000 Units/Reel
LBC848BDW1T3G	1K	10000 Units/Reel
LBC848CDW1T1G	1L	3000 Units/Reel
LBC848CDW1T3G	1L	10000 Units/Reel

LBC846ADW1T1G Series
S-LBC846ADW1T1G Series

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage ($I_C = 10\text{ mA}$)	$V_{(BR)CEO}$				V
LBC846 Series		65	—	—	
LBC847 Series		45	—	—	
LBC848 Series		30	—	—	
Collector–Emitter Breakdown Voltage ($I_C = 10\ \mu\text{A}$, $V_{EB} = 0$)	$V_{(BR)CES}$				V
LBC846 Series		80	—	—	
LBC847 Series		50	—	—	
LBC848 Series		30	—	—	
Collector–Base Breakdown Voltage ($I_C = 10\ \mu\text{A}$)	$V_{(BR)CBO}$				V
LBC846 Series		80	—	—	
LBC847 Series		50	—	—	
LBC848 Series		30	—	—	
Emitter–Base Breakdown Voltage ($I_E = 1.0\ \mu\text{A}$)	$V_{(BR)EBO}$				V
LBC846 Series		6.0	—	—	
LBC847 Series		6.0	—	—	
LBC848 Series		5.0	—	—	
Collector Cutoff Current ($V_{CB} = 30\text{ V}$)	I_{CBO}	—	—	15	nA
($V_{CB} = 30\text{ V}$, $T_A = 150^\circ\text{C}$)		—	—	5.0	μA

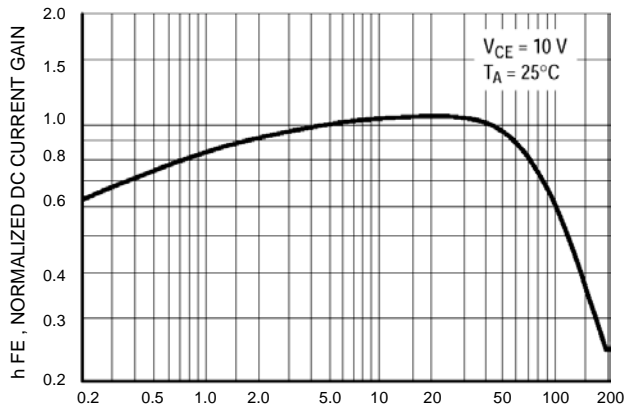
ON CHARACTERISTICS

DC Current Gain ($I_C = 2.0\text{ mA}$, $V_{CE} = 5.0\text{ V}$)	h_{FE}				—
LBC846A		110	180	220	
LBC846B, LBC847B, LBC848B		200	290	450	
LBC847C, LBC848C		420	520	800	
Collector–Emitter Saturation Voltage ($I_C = 10\text{ mA}$, $I_B = 0.5\text{ mA}$)	$V_{CE(sat)}$	—	—	0.25	V
($I_C = 100\text{ mA}$, $I_B = 5.0\text{ mA}$)		—	—	0.6	
Base–Emitter Saturation Voltage ($I_C = 10\text{ mA}$, $I_B = 0.5\text{ mA}$)	$V_{BE(sat)}$	—	0.7	—	V
($I_C = 100\text{ mA}$, $I_B = 5.0\text{ mA}$)		—	0.9	—	
Base–Emitter Voltage ($I_C = 2.0\text{ mA}$, $V_{CE} = 5.0\text{ V}$)	$V_{BE(on)}$	580	660	700	mV
($I_C = 10\text{ mA}$, $V_{CE} = 5.0\text{ V}$)		—	—	770	

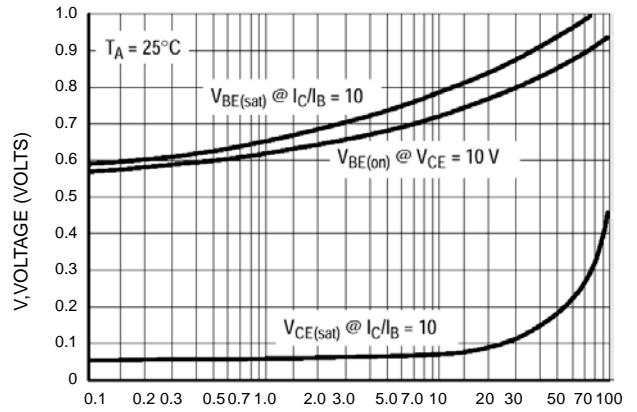
SMALL–SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product ($I_C = 10\text{ mA}$, $V_{CE} = 5.0\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	100	—	—	MHz
Output Capacitance ($V_{CB} = 10\text{ V}$, $f = 1.0\text{ MHz}$)	C_{obo}	—	—	4.5	pF
Noise Figure ($I_C = 0.2\text{ mA}$, $V_{CE} = 5.0\text{ Vdc}$, $R_S = 2.0\text{ k}\Omega$, $f = 1.0\text{ kHz}$, $BW = 200\text{ Hz}$)	NF				dB
LBC846A, LBC846B, LBC847B, LBC848B		—	—	10	
LBC847C, LBC848C		—	—	4.0	

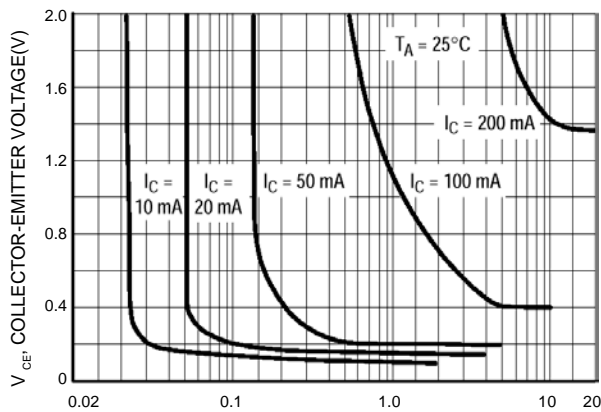
TYPICAL CHARACTERISTICS



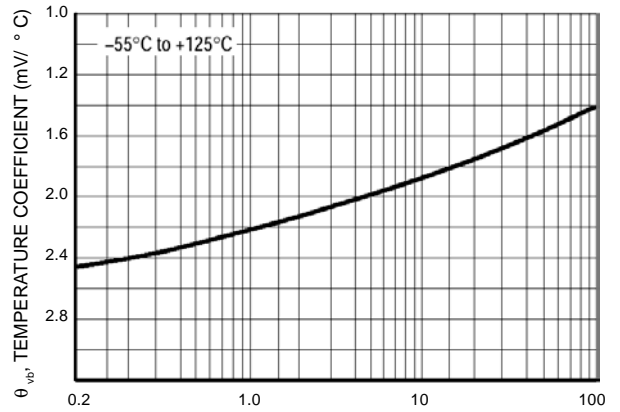
IC, COLLECTOR CURRENT (mA)
Figure 1. Normalized DC Current Gain



IC, COLLECTOR CURRENT (mA)
Figure 2. "Saturation" and "On" Voltages

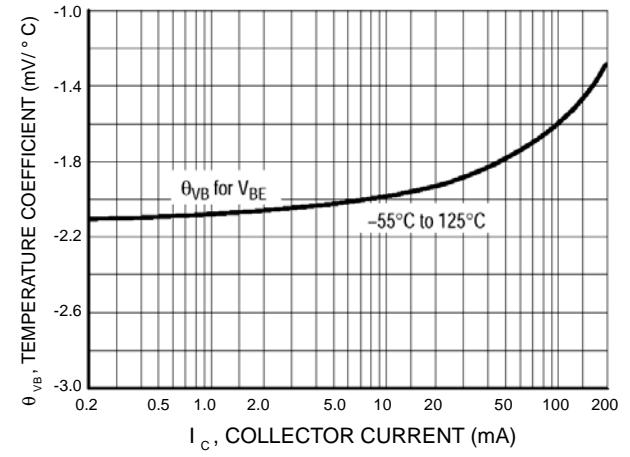
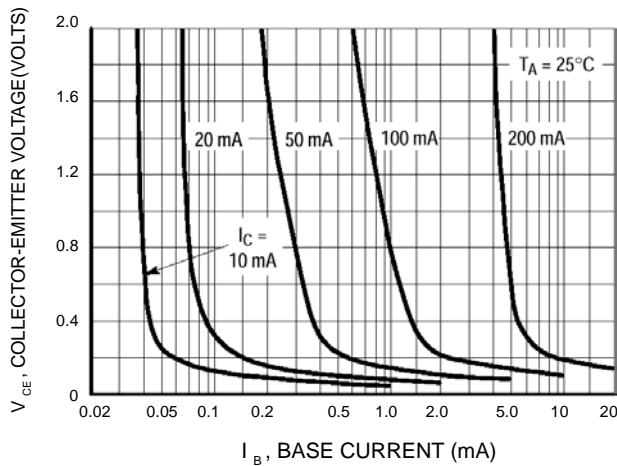
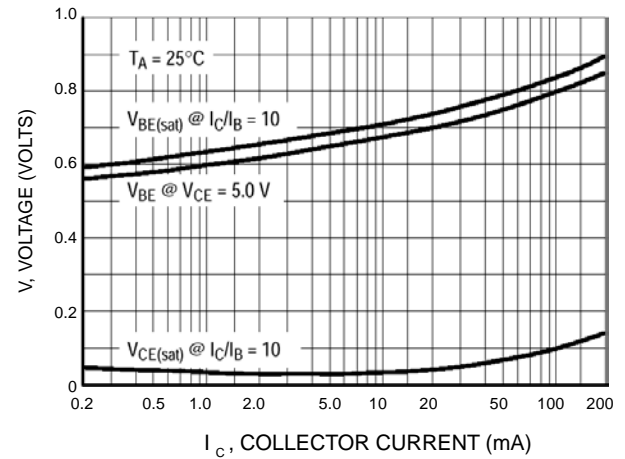
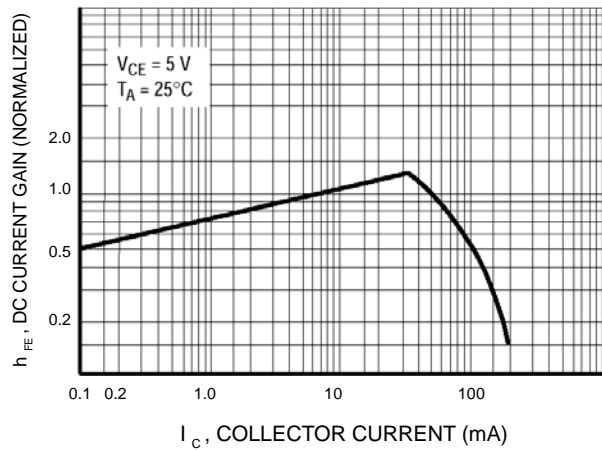
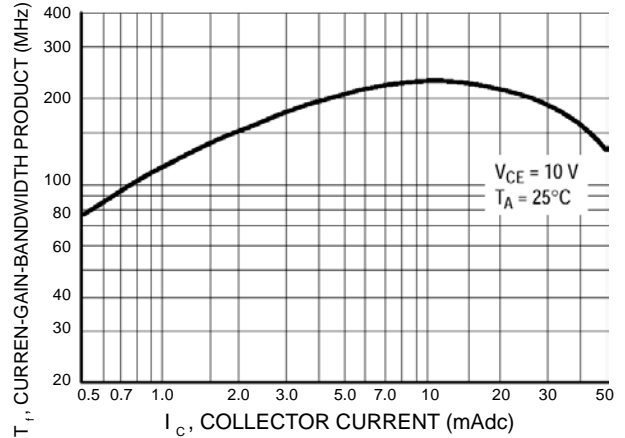
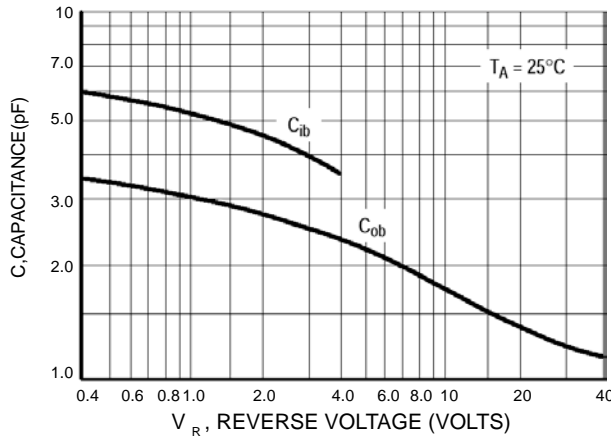


IB, BASE CURRENT (mA)
Figure 3. Collector Saturation Region



IC, COLLECTOR CURRENT (mA)
Figure 4. Base-Emitter Temperature Coefficient

TYPICAL CHARACTERISTICS



LBC846ADW1T1G Series
S-LBC846ADW1T1G Series

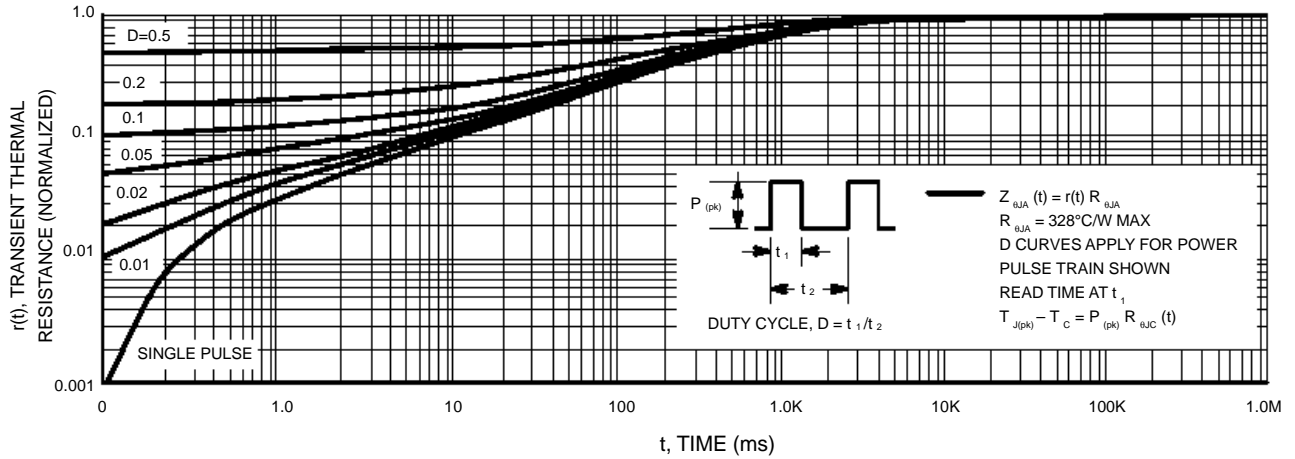


Figure 11. Thermal Response

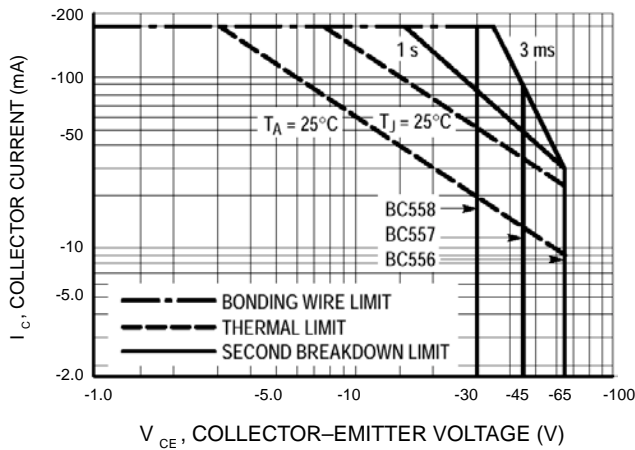


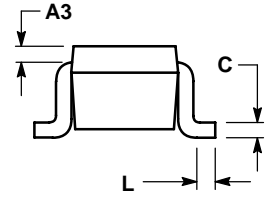
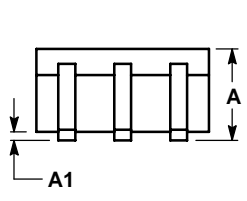
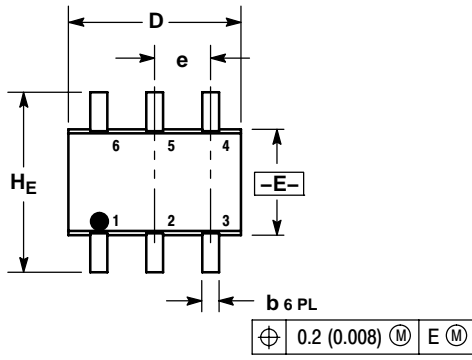
Figure 12. Active Region Safe Operating Area

The safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 12 is based upon $T_{J(pk)} = 150^\circ\text{C}$; T_C or T_A is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^\circ\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 12. At high case or ambient temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by the secondary breakdown.

LBC846ADW1T1G Series
S-LBC846ADW1T1G Series

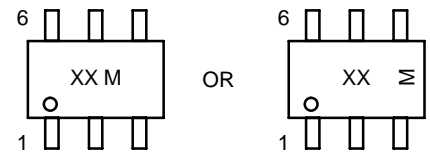
SC-88



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. 419B-01 OBSOLETE, NEW STANDARD 419B-02.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.95	1.10	0.031	0.037	0.043
A1	0.00	0.05	0.10	0.000	0.002	0.004
A3	0.20 REF			0.008 REF		
b	0.10	0.21	0.30	0.004	0.008	0.012
C	0.10	0.14	0.25	0.004	0.005	0.010
D	1.80	2.00	2.20	0.070	0.078	0.086
E	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65 BSC			0.026 BSC		
L	0.10	0.20	0.30	0.004	0.008	0.012
HE	2.00	2.10	2.20	0.078	0.082	0.086

GENERIC MARKING DIAGRAM*



XX = Specific Device Code
 M = Date Code